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CLAIMS

What is claimed is:

MOSFETs.

BA2)	1	1. An active pixel sensor circuit comprising:
/	2	a photodetector;
	3	a reset transistor connected between the photodetector and a first bus
	4	a snapshot transistor having a node connected to the photodetector;
	5	a driver transistor connected to a second bus and the snapshot
	6	transistor; and
	7	an isolation transistor connected between the driver transistor and a
<u>.</u>	8	column bus.
	1	2. The active pixel sensor circuit of Claim 1, wherein the transistors are

- 3. The active pixel sensor circuit of Claim 2, wherein a tapered reset signal is applied to the reset transistor in order to reset the photodiode.
- 4. The active pixel sensor circuit of Claim 3, wherein a charge from the photodiode is transferred to a gate capacitance of the driver transistor via the snapshot transistor.
- 5. The active pixel sensor circuit of Claim 4, wherein the reset transistor discharges any charge left on the photodetector along with any charge on the gate of the driver transistor during a reset operation.
- 6. The active pixel sensor circuit of Claim 5, wherein the reset transistor is disabled during a signal integration mode and a snapshot image capture mode.
- 7. The active pixel sensor circuit of Claim 6, wherein, after snapshot image capture, the reset transistor is enabled in order to drain any unwanted charge that is generated after the integration mode.

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1	8. The active pixel sensor circuit of Claim 7, further comprising a column
2	buffer connected to the column bus.
1	9. The active pixel sensor circuit of Claim 8, further comprising a row driver
2	circuit connected to the driver transistor.
1	10. An active pixel sensor circuit comprising:
2	photodetector means for converting light into an electrical signal;
3	image snapshot means connected to the photodetector for transferring
4	the signal from the photodetector;
5	reset means for resetting the photodetector after the image has been
6	transferred;
7	amplifier means for amplifying the signal from the snapshot means;
8	and
9	isolation means for isolating the circuit from a column bus.
1	11. A method for snapshot image formation in an active pixel sensor, the
2	method comprising:
3	resetting a photodetector;
4	integrating a charge signal on the photodetector;
5	transferring the charge signal from the photodetector to a capacitance
6	via a snapshot transistor; and
7	reading out the signal to a bus.
	12. The method of Claim 11, wherein the photodetector is reset with a tapered
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2	clock signal.
1	13. The method of Claim 12, wherein the capacitance is a gate capacitance on
2	a driver transistor.

1	14. A CMOS imager array comprising a plurality of pixels, each pixel
2	comprising:
3	aphotodetector;
4	a reset MOSFET having a source connected to the photodetector, a
5	gate connected to a reset input signal, and a drain connected to a first bus;
6	a snapshot MOSFET having a source connected to the photodetector
7	and a gate connected to a snapshot signal;
8	a driver MOSFET having a drain connected to a second bus and a gate
9	connected to a drain of the snapshot MOSFET;
10	an isolation MOSRET having a drain connected to a source of the
11	driver MOSFET, a gate connected to an access signal, and a source connected to a
12	column bus.
1	15. The imager array of Claim 14, wherein the reset, snapshot, driver and
2	isolation MOSFETs are all of the same polarity.
1	16. The imager array of Claim 15, further comprising a row driver circuit
2	connected to the second bus.
1	17. The imager array of Claim 16, further comprising a column buffer circuit
2	connected to the column bus.
1	18. A CMOS imager array having a plurality of active pixel cells, each cell
2	having a photodetector, the improvement comprising a snapshot transistor to transfer a
3	charge from the photodetector to a driver transistor, when a snapshot signal is
4	received.